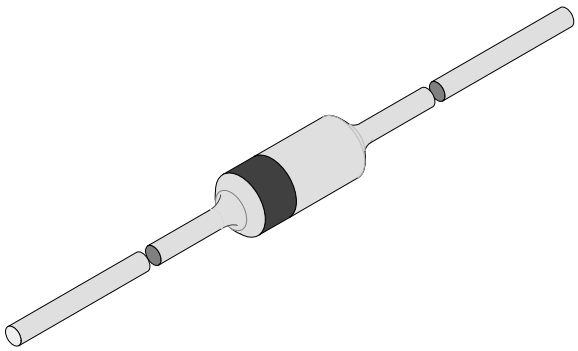
1N746A...1N759A

Silicon Z–Diodes

Features

- Very sharp reverse characteristic
- Very high stability
- Low reverse current level
- V_Z–tolerance ± 5%



94 9367

Applications

Voltage stabilization

Absolute Maximum Ratings

T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Value	Unit
Power dissipation	$T_L \leqq 75$˚C		P_V	500	mW
Z–current			I_Z	P_V/V_Z	mA
Junction temperature			T_j	200	˚C
Storage temperature range			T_{stg}	–65...+200	˚C

Maximum Thermal Resistance

T_j = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	l=9.5mm (3/8”), T_L=constant	R_{thJA}	300	K/W

Characteristics

T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=200mA		V_F			1.1	V

Type	V_{Znom} [1]	I_{ZT} for	r_{zjT}	I_R and	I_{R1} * at	V_R	TK_{VZ}
	V	mA	Ω	µA max	µA max	V	%/K
1N746A	3.3	20	< 28	10	30	1.0	< +0.091
1N747A	3.6	20	< 24	10	30	1.0	< +0.091
1N748A	3.9	20	< 23	10	30	1.0	< +0.092
1N749A	4.3	20	< 22	2	30	1.0	< +0.093
1N750A	4.7	20	< 19	2	30	1.0	< +0.094
1N751A	5.1	20	< 17	1	20	1.0	< +0.095
1N752A	5.6	20	< 11	1	10	1.0	< +0.095
1N753A	6.2	20	< 7	0.1	10	1.0	< +0.096
1N754A	6.8	20	< 5	0.1	20	1.0	< +0.096
1N755A	7.5	20	< 6	0.1	20	1.0	< +0.097
1N756A	8.2	20	< 8	0.1	20	1.0	< +0.097
1N757A	9.1	20	< 10	0.1	20	1.0	< +0.097
1N758A	10	20	< 17	0.1	20	1.0	< +0.098
1N759A	12	20	< 30	0.1	20	1.0	< +0.098

[1] Based on dc measurement at thermal equilibrium;
lead length = 9.5 mm ($^3/_8$ ");
thermal resistance of heat sink = 30 K/W.

* T_j = 150˚C

Dimensions in mm

technical drawings
according to DIN
specifications

94 9366

Standard Glass Case
54 A 2 DIN 41880
JEDEC DO 35
Weight max. 0.3 g